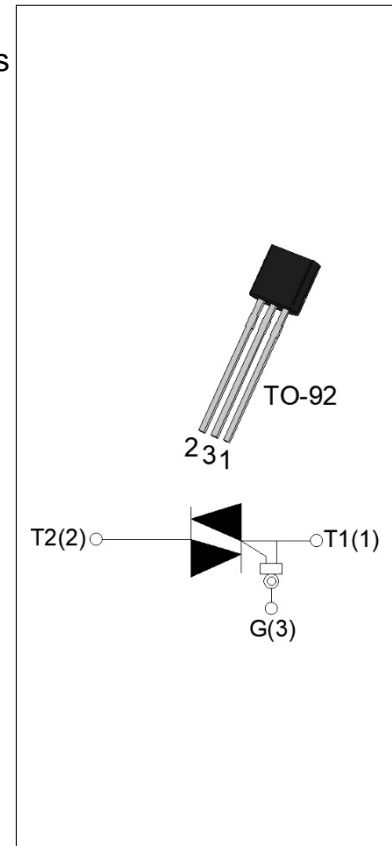


DESCRIPTION:

The JPTT01U-800SW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The JPTT01U-800SW embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. At the same time, the triac shields the positive signal trigger to reduce the probability of product misoperation. It is triggered with a negative gate current flowing out of the gate pin. Package TO-92 is RoHS compliant.


MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\ II/III}$	10/10	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c \leq 53^\circ\text{C}$)	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	14	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		15.4	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	0.98	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	di/dt	100	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	1	A
Positive applied gate voltage	V_{GM}	15	V

Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.1	W
Peak gate power	P_{GM}	2	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	2.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	II-III	MAX.	10	mA
V_{GT}		II-III	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	II-III	MIN.	0.15	V
I_L	$I_G=1.2I_{GT}$	II	MAX.	40	mA
		III		20	
I_H	$I_T=100\text{mA}$		MAX.	20	mA
dV/dt	$V_D=540\text{V}$ Gate Open $T_j=125^\circ\text{C}$		MIN.	1000	V/ μs
(dI/dt) _c	(dV/dt) _c =15V/ μs , $T_j=125^\circ\text{C}$		MIN.	2	A/ms
t_{on}	$I_G=20\text{mA } I_A=200\text{mA } I_R=20\text{mA}$ $T_j=25^\circ\text{C}$		TYP.	2.5	μs
t_{off}				25	
V_{CL}	$I_{CL}=0.1\text{mA } t_p=1\text{ms}$		MIN.	950	V

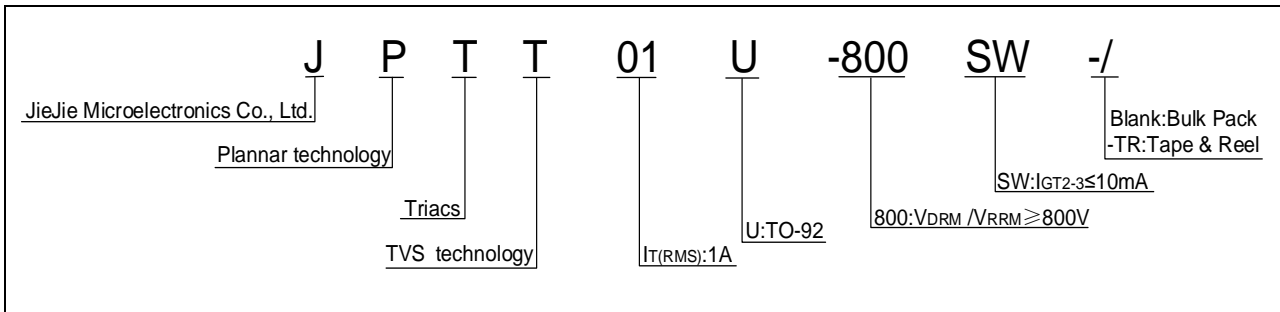
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=1.1\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.34	V
V_{TO}	Threshold voltage	$T_j=125^\circ\text{C}$	0.79	V
R_D	Dynamic resistance	$T_j=125^\circ\text{C}$	429	m Ω
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	2	μA
I_{RRM}		$T_j=125^\circ\text{C}$	0.2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	55	$^\circ\text{C/W}$
$R_{th(j-a)}$	junction to ambient (AC)	150	$^\circ\text{C/W}$

ORDERING INFORMATION



MARKING

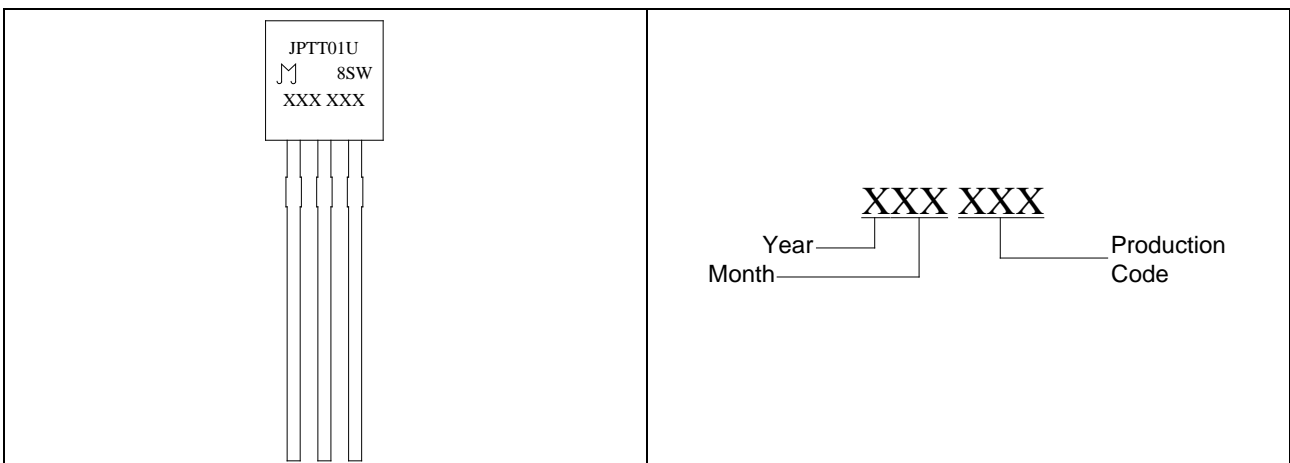


FIG.1 Maximum power dissipation versus RMS on-state current

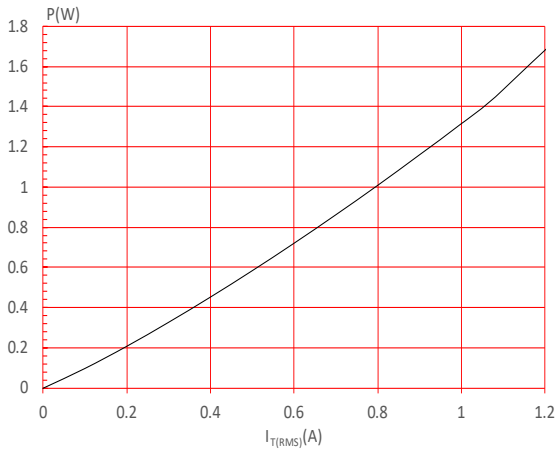


FIG.2: RMS on-state current versus case temperature

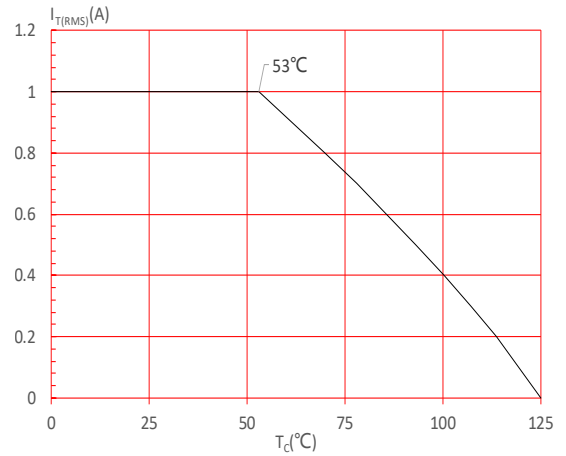


FIG.3: Surge peak on-state current versus number of cycles

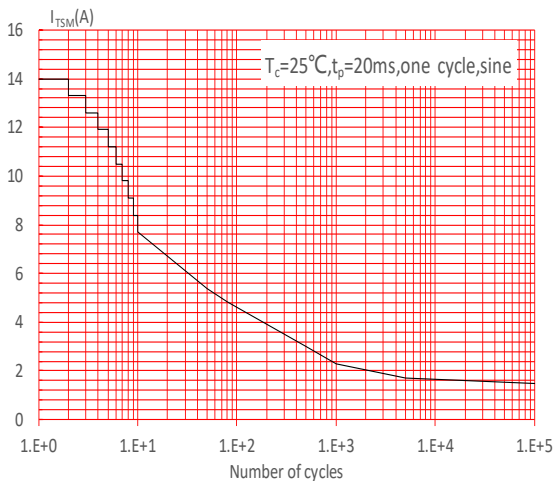


FIG.4: On-state characteristics

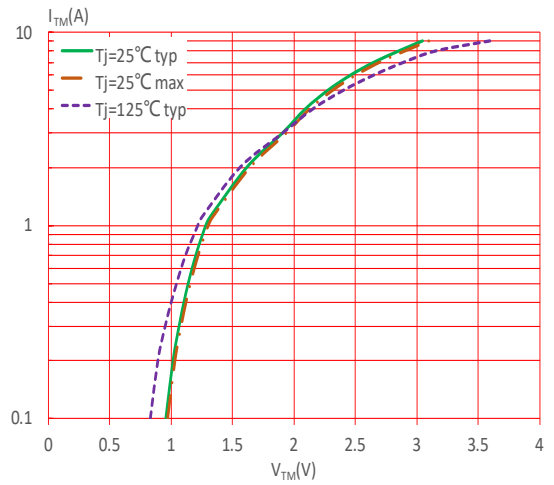


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

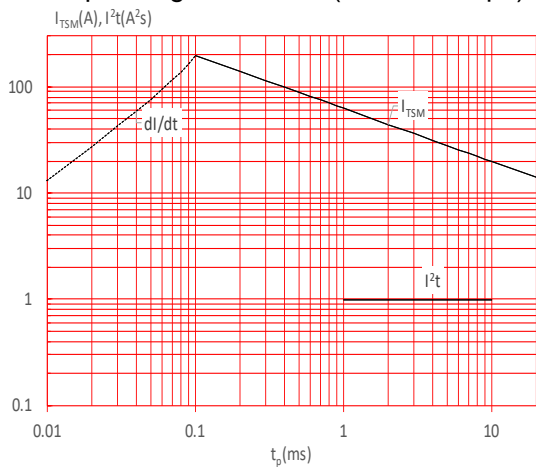


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

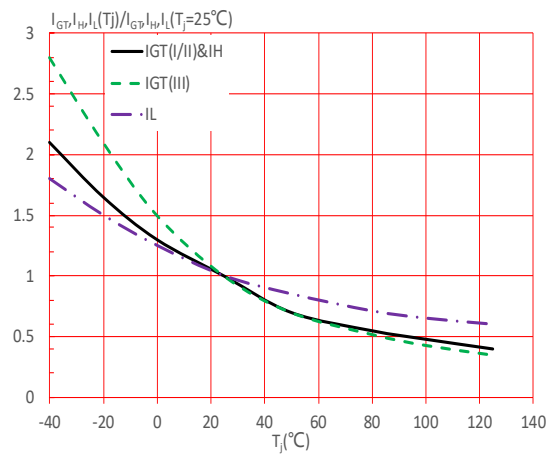
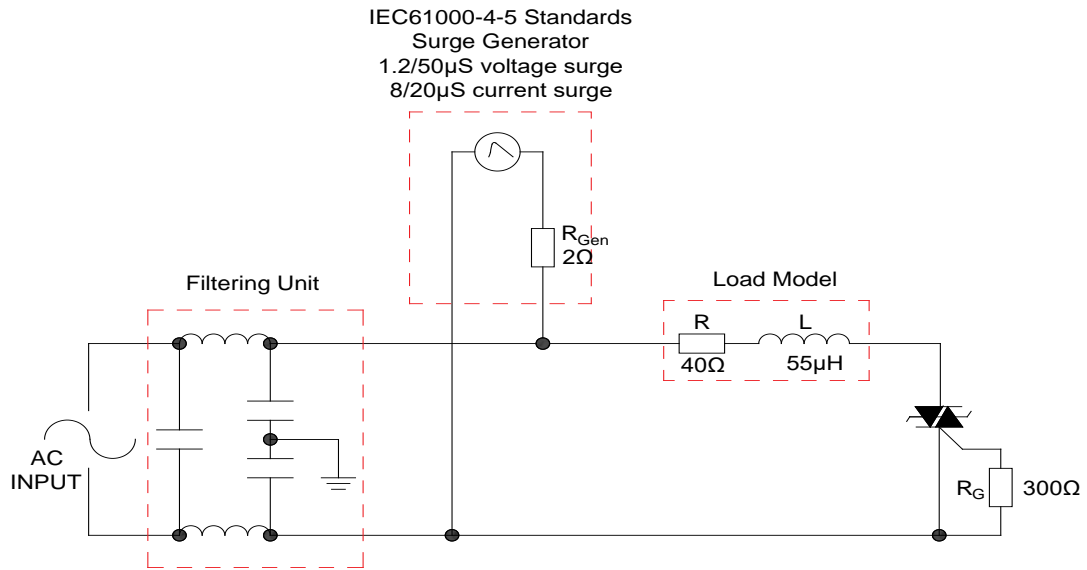


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

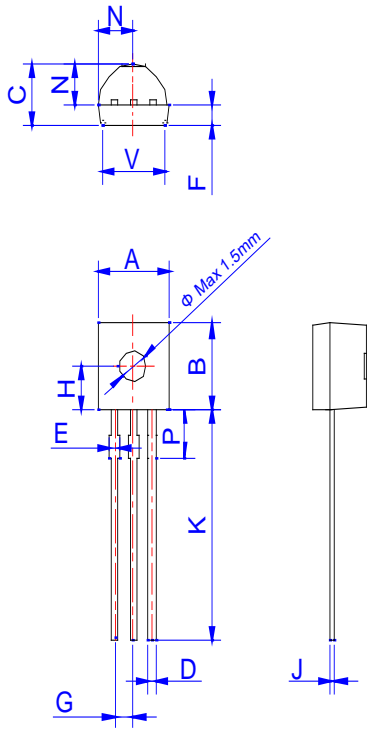
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JPTT01U-800SW	800	10	TO-92	1,000	Bulk Pack
JPTT01U-800SW-TR				2,000	Tape & Reel

Document Revision History

Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated

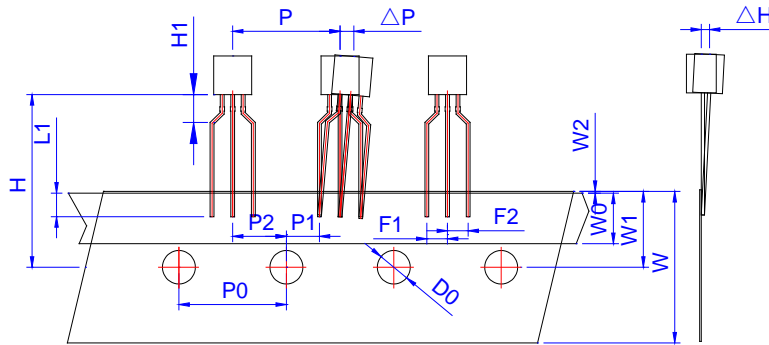
PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.45		5.20	0.175		0.205
B	4.32		5.33	0.170		0.210
C	3.18		4.19	0.125		0.165
D	0.407		0.533	0.016		0.021
E	0.50		0.70	0.020		0.028
F	1.10		1.30			0.051
G	1.10		1.40	0.043		0.055
H	2.20		2.40	0.087		0.094
J	0.36		0.50	0.014		0.020
K	12.70		15.0	0.500		0.591
N	2.04		2.66	0.080		0.105
P	1.80		2.30	0.071		0.091
V	4.10		4.50	0.161		0.177

DELIVERY MODE

PACKAGE	OUTLINE	BAG (PCS)	INNER BOX (PCS)	CARTON BOX (PCS)
TO-92	Bulk Pack	1,000	10,000	50,000




Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
P	12.40	12.70	13.00	0.488	0.500	0.512
P0	12.40	12.70	13.00	0.488	0.500	0.512
P1	3.55	3.85	4.15	0.140	0.152	0.163
P2	5.95	6.35	6.75	0.233	0.250	0.265
ΔP	-1.0	0	1.0	-0.039	0	0.039
F1、F2	2.30	2.50	2.70	0.090	0.098	0.106
F1-F2	-0.1	0	0.1	-0.004	0	0.004
W	17.50	18.00	19.00	0.689	0.709	0.748
W0	5.50	6.00	6.50	0.217	0.236	0.256
W1	8.50	9.00	9.50	0.335	0.354	0.374
W2			1.0			0.039
D0	3.80	4.0	4.20	0.150	0.157	0.165
ΔH	-1.0	0	1.0	-0.039	0	0.039
L1	2.5			0.098		
H	18.0	19.0	20.0	0.709	0.748	0.787
H1			2.70			0.106

PACKAGE	OUTLINE	REEL (PCS)	INNER BOX (PCS)	CARTON BOX (PCS)
TO-92	Tape & Reel	/	2,000	20,000

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